

45 V/60 V/80 V, 1 A PNP medium power transistors Rev. 1 — 19 June 2015 Produ

Product data sheet

#### **Product profile** 1.

### **1.1 General description**

PNP medium power transistor series encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and solderable side pads.

#### Table 1. **Product overview**

Type number <sup>[1]</sup>	Package	Package	
BC51PAS	DFN2020D-3	SOT1061D	BC54PAS
BC52PAS			BC55PAS
BC53PAS			BC56PAS

[1] Valid for all available selection groups.

### **1.2 Features and benefits**

- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Reduced Printed-Circuit Board (PCB) area requirements
- Exposed heat sink for excellent thermal and electrical conductivity
- AEC-Q101 qualified

### 1.3 Applications

- Linear voltage regulators
- Battery driven devices
- MOSFET drivers

### 1.4 Quick reference data

#### Quick reference data Table 2.

 $T_{amb} = 25 \ ^{\circ}C$  unless otherwise specified

anno =								
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit		
V <sub>CEO</sub>	collector-emitter voltage	open base						
	BC51PAS series		-	-	-45	V		
	BC52PAS series		-	-	-60	V		
	BC53PAS series		-	-	-80	V		



- Three current gain selections
- Leadless very small SMD plastic package with medium power capability
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- High-side switches
- Power management
- Amplifiers

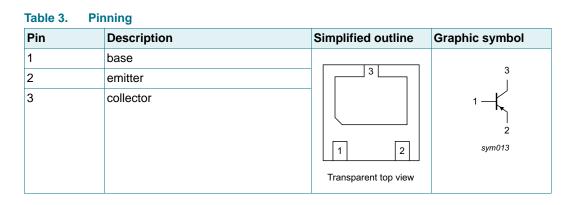
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#### Table 2. Quick reference data ...continued

Symbol	Deremeter	Conditions		Min	Turn	Max	Unit
Symbol	Parameter	Conditions		wiin	Тур	Мах	Unit
I <sub>C</sub>	collector current			-	-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-	-2	А
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -150 \text{ mA}$	[1]	63	-	250	
	h <sub>FE</sub> selection -10	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	63	-	160	
	h <sub>FE</sub> selection -16	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -150 \text{ mA}$	<u>[1]</u>	100	-	250	

[1] Pulse test:  $t_p \le 300 \text{ ms}; \delta \le 0.02.$ 

### 2. Pinning information



## 3. Ordering information

#### Table 4. Ordering information

Type number <sup>[1]</sup>	Package				
	Name	Description	Version		
BC51PAS series			SOT1061D		
BC52PAS series		outline package; no leads; 3 terminals; body $2 \times 2 \times 0.65$ mm.			
BC53PAS series	1	body 2 × 2 × 0.05 mm.			

[1] Valid for all available selection groups.

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### 4. Marking

Table 5.Marking codes	
Type number	Marking code
BC51PAS	C4
BC51-10PAS	C5
BC51-16PAS	C6
BC52PAS	C7
BC52-10PAS	C8
BC52-16PAS	C9
BC53PAS	CA
BC53-10PAS	СВ
BC53-16PAS	CC

## 5. Limiting values

#### Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC51PAS series		-	-45	V
	BC52PAS series		-	-60	V
	BC53PAS series		-	-100	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC51PAS series		-	-45	V
	BC52PAS series		-	-60	V
	BC53PAS series		-	-80	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-5	V
I <sub>C</sub>	collector current		-	-1	A
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-2	А
I <sub>B</sub>	base current		-	-0.3	А

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Table 6. Limiting	values	continued
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In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>	-	0.42	W
			[2]	-	0.81	W
			[3]	-	0.83	W
			[4]	-	1.10	W
			[5]	-	1.65	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

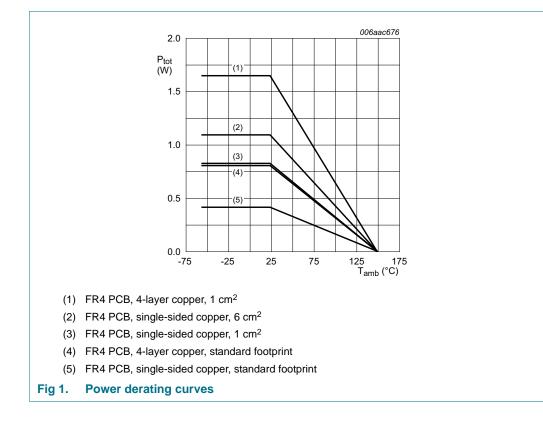
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.



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### 6. Thermal characteristics

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Symbol	Parameter	Conditions		Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u>	298	K/W
			[2]	154	K/W
			[3]	151	K/W
			[4]	114	K/W
			[5]	76	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	in free air		20	K/W

#### Table 7. Thermal characteristics

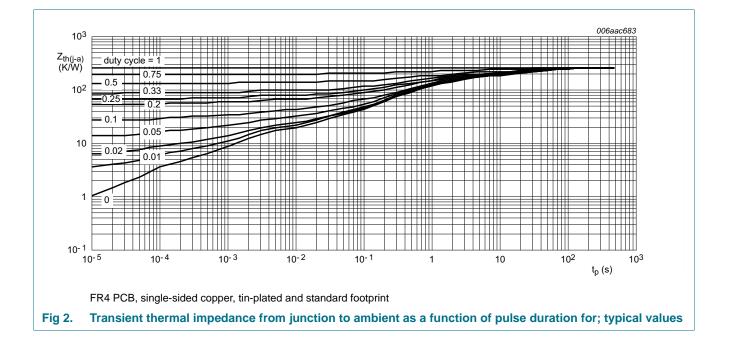
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm<sup>2</sup>.

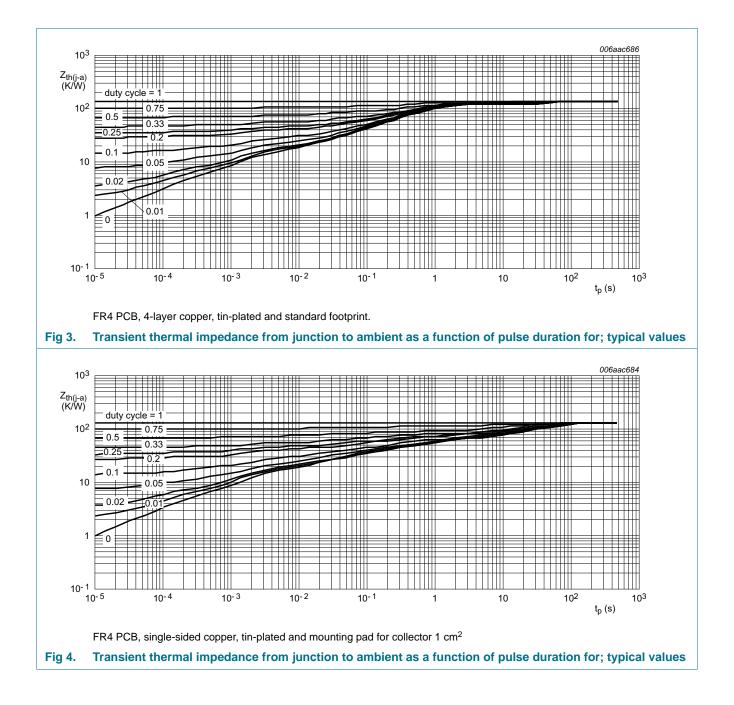
[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm<sup>2</sup>



### **NXP Semiconductors**

## BC51PAS; BC52PAS; BC53PAS

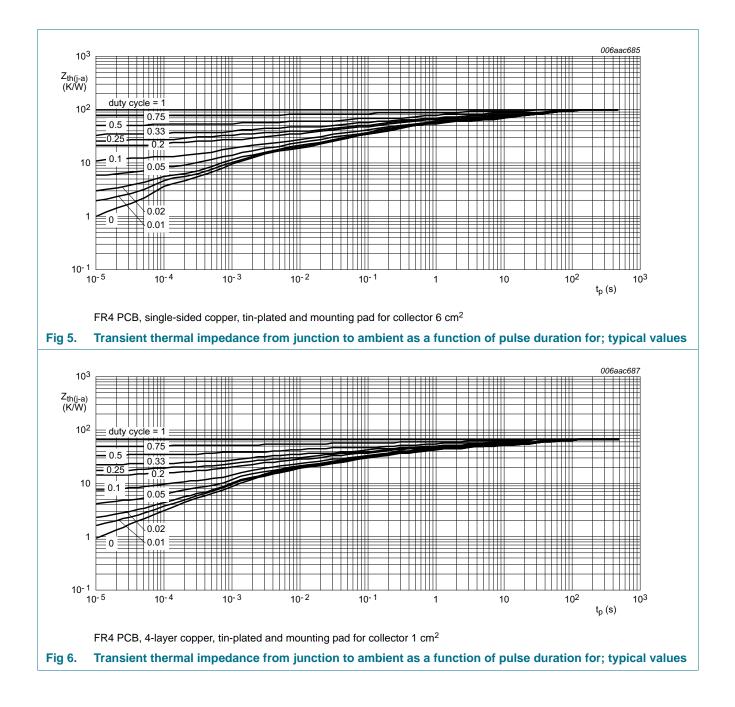
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### **NXP Semiconductors**

## BC51PAS; BC52PAS; BC53PAS

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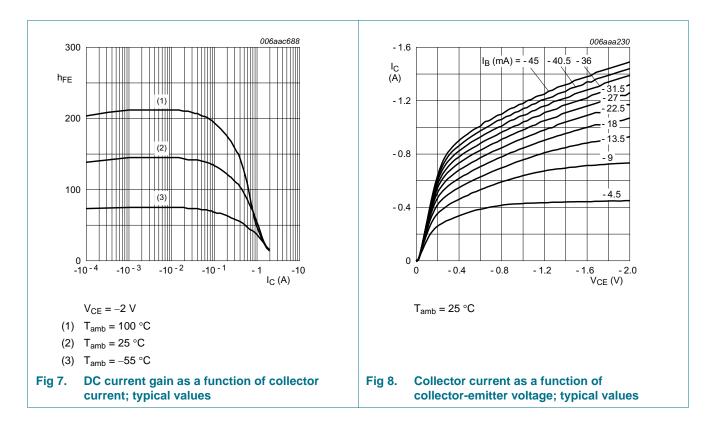
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## 7. Characteristics

#### Table 8. Characteristics

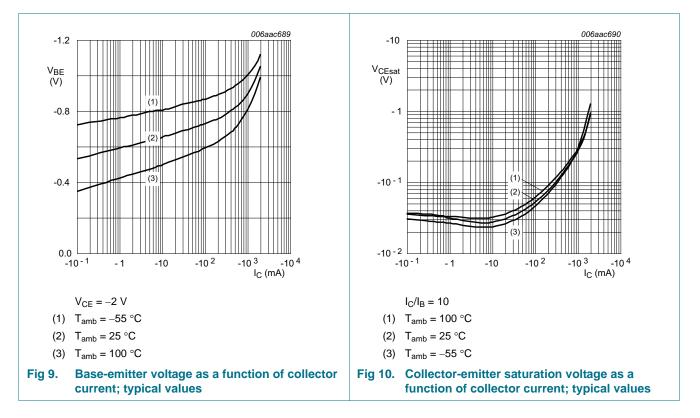
 $T_{amb} = 25 \ ^{\circ}C$  unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}$		-	-	-100	nA
		$V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$		-	-	-10	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -5 \text{ mA}$		63	-	-	
h <sub>FE</sub> selection -10		$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -150 \text{ mA}$	<u>[1]</u>	63	-	250	
		$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -500 \text{ mA}$	<u>[1]</u>	40	-	-	
	h <sub>FE</sub> selection -10	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -150 \text{ mA}$	<u>[1]</u>	63	-	160	
	h <sub>FE</sub> selection -16	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -150 \text{ mA}$	<u>[1]</u>	100	-	250	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{\rm C}$ = -500 mA; $I_{\rm B}$ = -50 mA	<u>[1]</u>	-	-	-500	mV
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -500 \text{ mA}$	<u>[1]</u>	-	-	-1	V
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A}; \text{ f} = 1 \text{ MHz}$		-	15	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -50 \text{ mA}; \text{ f} = 100 \text{ MHz}$		-	145	-	MHz



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### 8. Test information

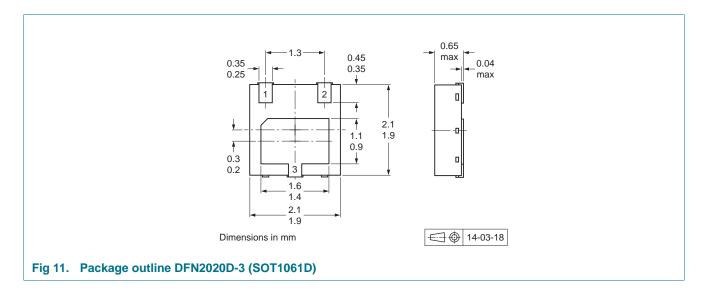
#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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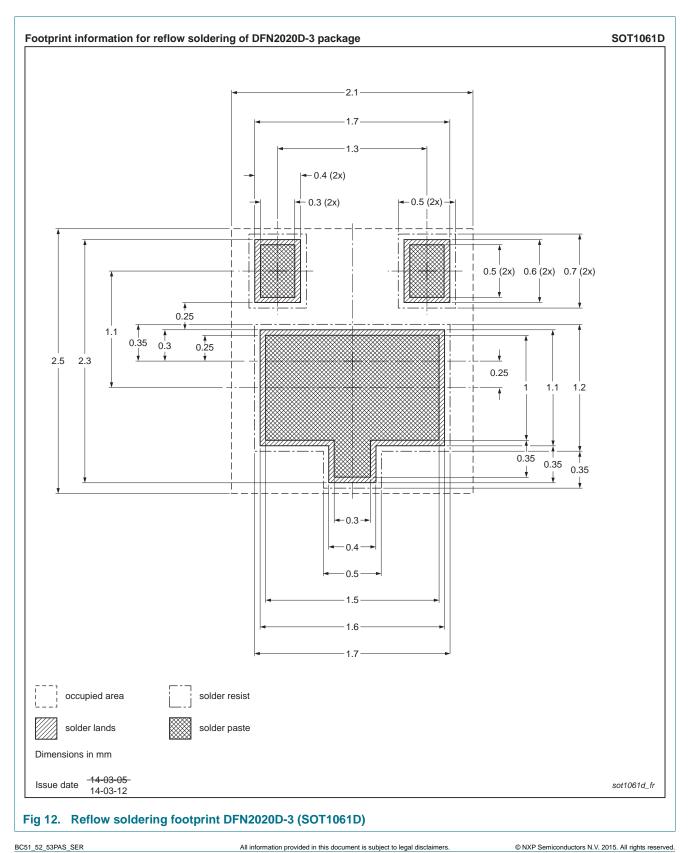
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## 9. Package outline



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## **10. Soldering**



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## **11. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC51_52_53PAS_SER v.1	20150619	Product data sheet	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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